

CL74LVC2G14 Dual Schmitt-Trigger Inverter

General Description

This dual Schmitt-trigger inverter is designed for 1.65-V to 5.5-V V_{CC} operation.

The CL74LVC2G14 device contains two inverters and performs the Boolean function $Y = \overline{A}$. The device functions as two independent inverters, but because of Schmitt action, it may have different input threshold levels for positive-going (V_{T+}) and negative-going (V_{T-}) signals.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Ordering Information

Part Number	Package	
CL74LVC2G14	SOT-23-6	
	SOT-25	
	SOT-353	
	SOT-553	

Features

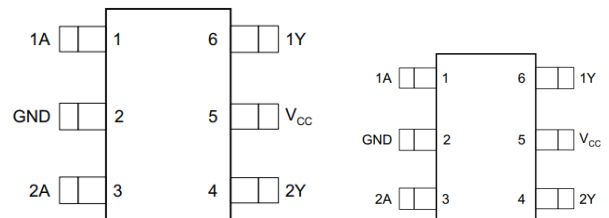
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max T_{pd} of 5.4 ns at 3.3 V
- Low Power Consumption, 10- μ A Maximum I_{CC}
- ± 24 -mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at $V_{CC} = 3.3$ V, $T_A = 25^\circ\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at $V_{CC} = 3.3$ V, $T_A = 25^\circ\text{C}$

- I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 1000-V Charged-Device Model (C101)

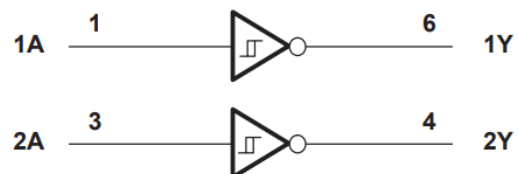
Applications

- Body Control Modules
- Engine Control Modules
- Arcade, Casino, and Gambling Machines
- Servers and High-Performance Computing
- EPOS, ECR, and Cash Drawer
- Desktop PC

Pin Configuration



Simplified Schematic





Pin Assignment

CL74LVC2G14

Pin Name	Pin No.	Pin Function
GND	2	Ground
1A	1	Input 1
2A	3	Input 2
1Y	6	Open-drain output 1
2Y	4	Open-drain output 2
Vcc	5	Power pin

Absolute Maximum Ratings (Note1)

- V_{CC} ----- -0.5V to +6.5V
- V_I ----- -0.5V to +6.5V
- V_O (Voltage range applied to any output in the high-impedance or power-off state)----- -0.5V to +6.5V
- V_O (Voltage range applied to any output in the high or slow state)----- -0.5V to $V_{CC}+0.5V$
- Input clamp current ----- -50mA
- Output clamp current ----- -50mA
- Continuous output current ----- $\pm 50mA$
- Storage Temperature ----- $-65^{\circ}C$ to $150^{\circ}C$

Recommended Operating Conditions

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Supply voltage	V_{CC}	Operating	1.65		5.5	V
		Data retention only	1.5			
Input voltage	V_I		0		5.5	V
Output voltage	V_O		0		VCC	V
High- level output current	I_{OH}	$V_{CC} = 1.65V$			-4	mA
		$V_{CC} = 2.3V$			-8	
		$V_{CC} = 3V$			-16	
		$V_{CC} = 3V$			-24	
		$V_{CC} = 4.5V$			-32	
Low- level output current	I_{OL}	$V_{CC} = 1.65V$			4	mA
		$V_{CC} = 2.3V$			8	
		$V_{CC} = 3V$			16	
		$V_{CC} = 3V$			24	
		$V_{CC} = 4.5V$			32	
Operating temperature	T_A		-40		125	$^{\circ}C$

Electrical Characteristics

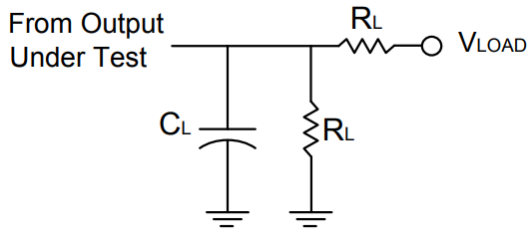
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Positive-going input threshold voltage	V_{T+}	$V_{CC} = 1.65V$	0.7		1.4	V
		$V_{CC} = 2.3V$	1		1.7	
		$V_{CC} = 3V$	1.3		2.2	

		$V_{CC} = 4.5V$	1.9	3.1	
		$V_{CC} = 5.5V$	2.2	3.7	
Negative-going input threshold voltage	V_T	$V_{CC} = 1.65V$	0.3	0.7	V
		$V_{CC} = 2.3V$	0.4	1	
		$V_{CC} = 3V$	0.6	1.3	
		$V_{CC} = 4.5V$	1.1	2	
		$V_{CC} = 5.5V$	1.4	2.5	
Hysteresis voltage	ΔV_T	$V_{CC} = 1.65V$	0.3	0.8	V
		$V_{CC} = 2.3V$	0.4	0.9	
		$V_{CC} = 3V$	0.4	1.1	
		$V_{CC} = 4.5V$	0.6	1.3	
		$V_{CC} = 5.5V$	0.7	1.4	
High- level output voltage	V_{OH}	$V_{CC} = 1.65\sim 5.5V, I_{OH} = 100\mu A$	VCC-0.1		V
		$V_{CC} = 1.65V, I_{OH} = 4mA$	1.2		
		$V_{CC} = 2.3V, I_{OH} = 8mA$	1.9		
		$V_{CC} = 3V, I_{OH} = 16mA$	2.4		
		$V_{CC} = 3V, I_{OH} = 24mA$	2.3		
		$V_{CC} = 4.5V, I_{OH} = 32mA$	3.8		
Low- level output voltage	V_{OL}	$V_{CC} = 1.65\sim 5.5V, I_{OL} = 100\mu A$		0.1	V
		$V_{CC} = 1.65V, I_{OL} = 4mA$		0.45	
		$V_{CC} = 2.3V, I_{OL} = 8mA$		0.3	
		$V_{CC} = 3V, I_{OL} = 16mA$		0.4	
		$V_{CC} = 3V, I_{OL} = 24mA$		0.55	
		$V_{CC} = 4.5V, I_{OL} = 32mA$		0.55	
Input leakage current	I_I	$V_{IN} = 5.5V$ or GND, $V_{CC} = 0\sim 5.5V$		± 5	μA
Power off leakage current	I_{OFF}	V_I or $V_O = 5.5V, V_{CC} = 0V$		± 10	μA
Supply current	I_{CC}	$V_{IN} = V_{CC}$ or GND, $I_{OUT} = 0, V_{CC} = 1.65\sim 5.5V$		10	μA
Additional supply current per input pin	ΔI_{CC}	$V_{CC} = 3\sim 5.5V$, one input at $V_{CC} - 0.6V$, other input at V_{CC} or GND		500	μA

Switching Characteristics

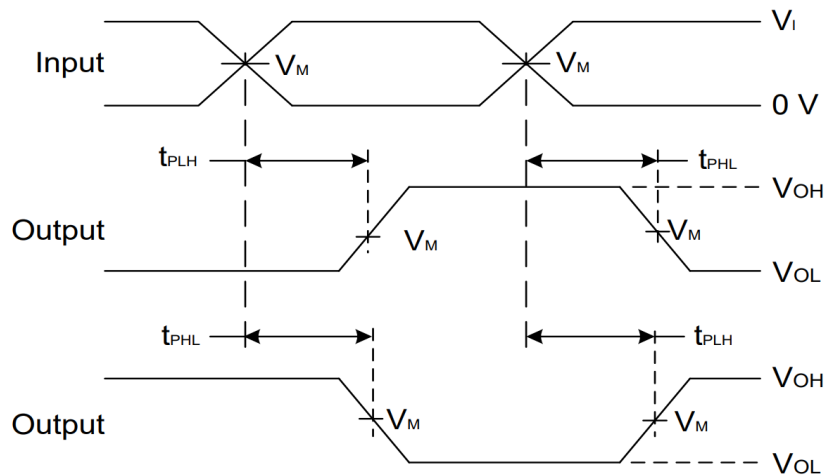
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Propagation delay from input(A or B) to output(Y)	T_{PD}	$V_{CC} = 1.8V \pm 0.15V, R_L = 1K\Omega$	3.9		9.5	ns
		$V_{CC} = 2.5V \pm 0.2V, R_L = 500\Omega$				
		$V_{CC} = 3.3V \pm 0.3V, R_L = 500\Omega$	2		5.4	
		$V_{CC} = 5V \pm 0.5V, R_L = 500\Omega$				

Parameter Measurement Information



TEST	Condition
t_{PLZ}	V_{LOAD}
t_{PZL}	V_{LOAD}

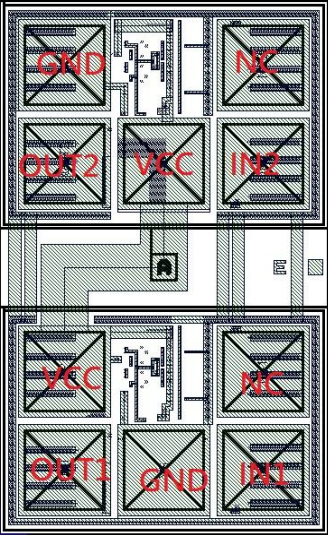
VCC	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8V \pm 0.15V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	$2 \times V_{CC}$	30pF	1k Ω	0.15V
$2.5V \pm 0.2V$	V_{CC}	$\leq 2ns$	$V_{CC}/2$	$2 \times V_{CC}$	30pF	500 Ω	0.15V
$3.3V \pm 0.3V$	3V	$\leq 2.5ns$	1.5V	6V	50pF	500 Ω	0.3V
$5V \pm 0.5V$	V_{CC}	$\leq 2.5ns$	$V_{CC}/2$	$2 \times V_{CC}$	50pF	500 Ω	0.3V



**Voltage Waveform Propagation Delay Times
Inverting and Non Inverting Outputs**

- Notes:
- A. C_L includes probe and jig capacitance
 - B. All pulses and supplied at pulse repetition rate $\leq 10MHz$
 - C. The Inputs are measured separately one transition per measurement
 - D. t_{PLH} and t_{PHL} are the same as t_{PD}

PAD Location and Coordinates

PHYSICAL CHARACTERISTICS		UNIT	CHIP DRAWING
Wafer Size	200	mm	
Die Size (with S/L)	0.308 * 0.466	mm ²	
Scribe line width	60	um	
TOP Metal thickness	3	um	
Top Metallization	Al-Cu		
Wafer Thickness	726	um	
CUP (circuit under PAD) or not	YES		
Bonding Wire Diameter	20	um	

PAD NAME	PAD SIZE (μm ²)	Coordinate
IN2	60*60	(199,282)
GND	60*60	(49,357)
GND	60*60	(124,49)
IN1	60*60	(199,49)
OUT1	60*60	(49,49)
VCC	60*60	(49,124)
OUT2	60*60	(49,282)

Bonding Diagram Example

